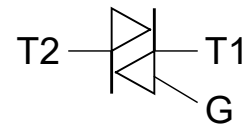
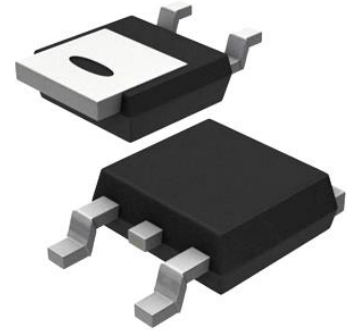


isc Thyristors

DESCRIPTION

- With TO-252(DPAK) packaging
- Operating in 3 quadrants
- High commutation capability
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

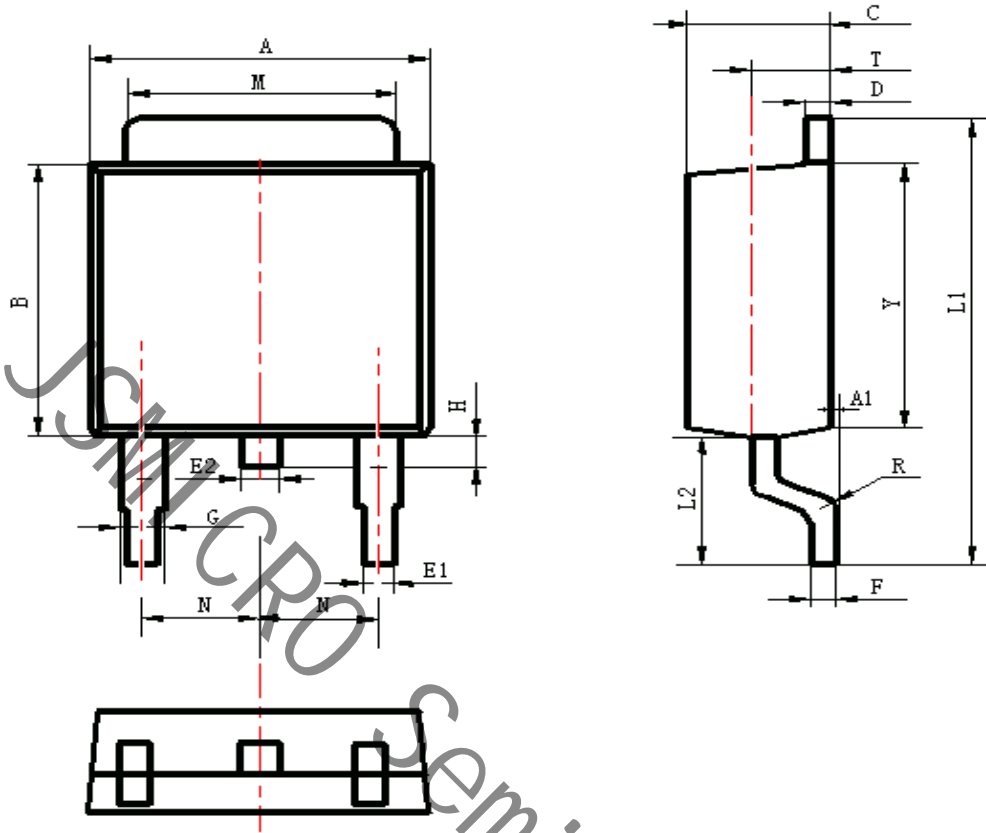
- Switching applications
- Phase control
- Motor control circuits
- Static switching on inductive or resistive load

ABSOLUTE MAXIMUM RATINGS (T_a=25°C)

SYMBOL	PARAMETER		MAX	UNIT
V _{DRM}	Repetitive peak off-state voltage		800	V
V _{RRM}	Repetitive peak reverse voltage		800	V
I _{T(RSM)}	Average on-state current		8	A
I _{TSM}	Surge non-repetitive on-state current	50HZ 60HZ	65 72	A
P _{G(AV)}	Average gate power dissipation (over any 20 ms period)		0.5	W
T _j	Operating junction temperature		-40~125	°C
T _{stg}	Storage temperature		-40~150	°C

ELECTRICAL CHARACTERISTICS (T_c=25°C unless otherwise specified)

SYMBOL	PARAMETER	CONDITIONS		MIN	MAX	UNIT
I _{RRM}	Repetitive peak reverse current	V _R =V _{RRM} Rated; V _D =V _{DRM} Rated;	T _j =125°C		0.5	mA
I _{DRM}	Repetitive peak off-state current					
V _{TM}	On-state voltage	I _T =10A			1.65	V
I _{GT}	Gate-trigger current	V _D =12V; I _T =0.1A;	I		50	mA
			II		50	
			III		50	
V _{GT}	Gate-trigger voltage	V _D =12V; I _T =0.1A;			1.5	V
R _{th (j-mb)}	Junction to mounting base	Half cycle			2.4	°C/W

Package Outline: TO-252


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	6.30	6.90	0.248	0.272
A1	0.00	0.16	0.000	0.006
B	5.70	6.30	0.224	0.248
C	2.10	2.50	0.083	0.098
D	0.30	0.70	0.012	0.028
E1	0.60	0.90	0.024	0.035
E2	0.70	1.00	0.028	0.039
F	0.30	0.60	0.012	0.024
G	0.70	1.20	0.028	0.047
L1	9.60	10.50	0.378	0.413
L2	2.70	3.10	0.106	0.122
H	0.40	1.00	0.016	0.039
M	5.10	5.50	0.201	0.217
N	2.09	2.49	0.082	0.098
R	0.30		0.012	
T	1.40	1.60	0.055	0.063
Y	5.10	6.30	0.201	0.248